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DSmall's Logan
PATENT
29936/37830
2/25/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Dae Gyu Park et al.)

Serial No.: 10/036,156)

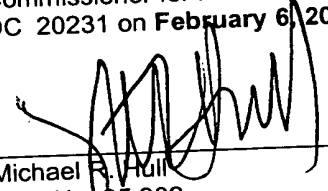
Filed: December 26, 2001)

For: Method of Forming a Metal
Gate in a Semiconductor Device
Using Atomic Layer Deposition
Process (as amended))

Group Art Unit: 2813)

Examiner: Jack S.J. Chen)

I hereby certify that this paper is being
deposited with the United States Postal
Service as first class mail, postage
prepaid, in an envelope addressed to:
Commissioner for Patents Washington,
DC 20231 on February 6, 2003


Michael R. Hull
Reg. No. 35,902
Attorney for Applicants

AMENDMENT

Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the Office Action dated November 06, 2002, the
following amendments and remarks are respectfully submitted in connection
with the above-identified application:

In the Specification:

Please replace the title with the following new title:

--METHOD OF FORMING A METAL GATE IN A SEMICONDUCTOR
DEVICE USING ATOMIC LAYER DEPOSITION PROCESS--

RECEIVED
FEB 11 2003
TECHNOLOGY CENTER 2800